

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

MCH6337 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- 1.8V drive
- · Protection diode in

- · Ultrahigh-speed switching
- · Halogen free compliance

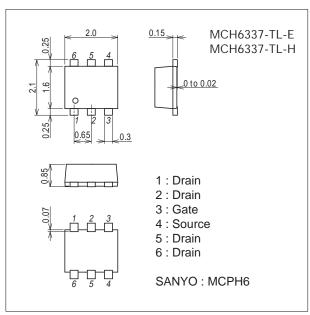
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-4.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-18	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² x0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7022A-009



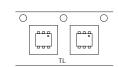
Product & Package Information

• Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

• Minimum Packing Quantity : 3,000 pcs./reel

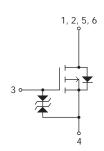
Packing Type: TL



Marking



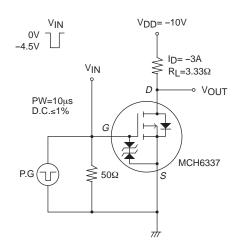
Electrical Connection



Electrical Characteristics at Ta=25°C

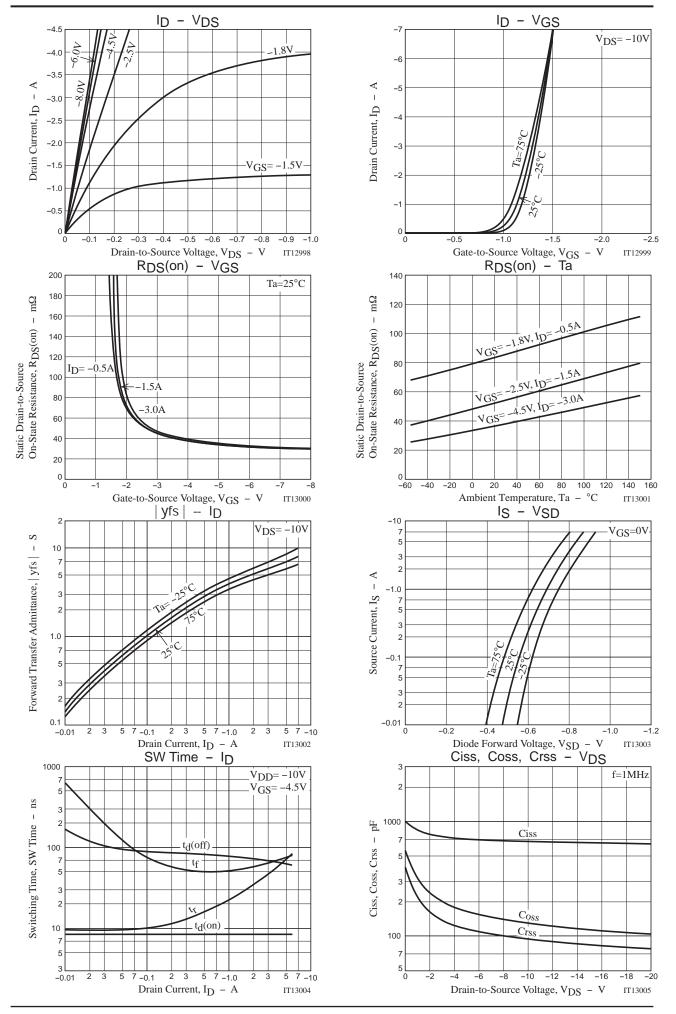
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Syllibol	Conditions	min	typ	max	Uniii	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V _D S=-10V, I _D =-3A	3.5	5.9		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-3A, V _G S=-4.5V		37	49	mΩ	
	R _{DS} (on)2	I _D =-1.5A, V _G S=-2.5V		53	75	mΩ	
	R _{DS} (on)3	I _D =-0.5A, V _G S=-1.8V		85	130	mΩ	
Input Capacitance	Ciss			670		pF	
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		130		pF	
Reverse Transfer Capacitance	Crss			94		pF	
Turn-ON Delay Time	t _d (on)			8.4		ns	
Rise Time	t _r	Considered Took Circuit		45		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		69		ns	
Fall Time	t _f			63		ns	
Total Gate Charge	Qg			7.3		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-4.5A		1.3		nC	
Gate-to-Drain "Miller" Charge	Qgd]		2.1		nC	
Diode Forward Voltage	V _{SD}	I _S =-4.5A, V _{GS} =0V		-0.82	-1.2	V	

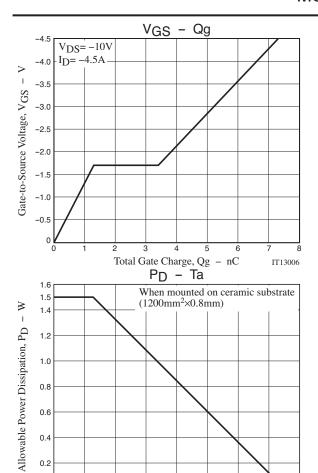
Switching Time Test Circuit



Ordering Information

Device	vice Package Shipping		memo	
MCH6337-TL-E	МСРН6	3,000pcs./reel	Pb Free	
MCH6337-TL-H	MCPH6	3,000pcs./reel	Pb Free and Halogen Free	





80

Ambient Temperature, Ta - °C

100

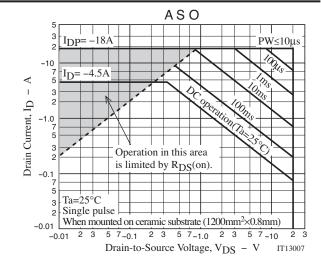
160

IT12997

0.2

0

20

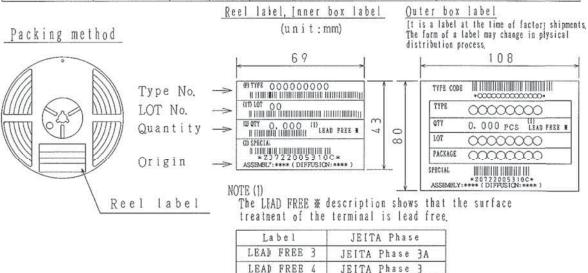


Taping Specification

MCH6337-TL-E, MCH6337-TL-H

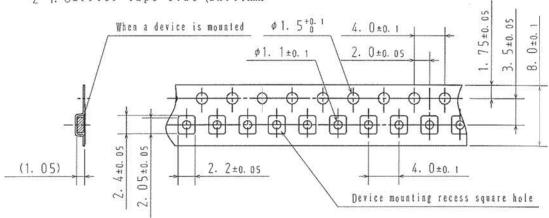
1. Packing Format

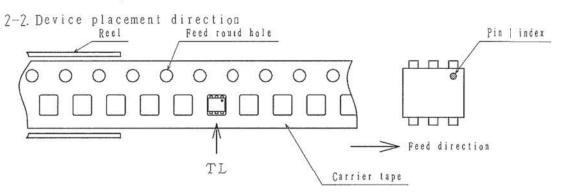
Package Name Carrier Tape Type	Carrier Tape	Maximum Number of devices contained (cs)			Packing format		
	Reel	[nner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
мсрн6	MCP4	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm(external) 440×195×210	



2. Taping configuration

2-1. Carrier tape size (unit:mm)





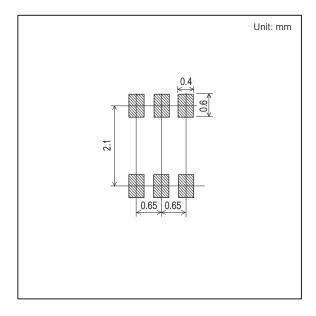
Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

MCH6337-TL-E, MCH6337-TL-H

Mass (g) Unit 0.008 mm 2.0±0.06 5 4 0.15±0.03 0.00.02 0.00.02 0.00.02 0.00.02 0.00.02 0.00.02 0.00.02 0.00.02

Land Pattern Example



Note on usage: Since the MCH6337 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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